# Jinn-Kong Sheu

List of Publications by Year
in descending order



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|---|---|---|---|
| 321 papers | 7,091 citations | 61945 43 h-index | 91828 69 g-index |
| 321 all docs | 321 docs citations | 321 times ranked | 4631 citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | White-light emission from near UV InGaN-GaN LED chip precoated with blue/green/red phosphors. IEEE Photonics Technology Letters, 2003, 15, 18-20. | 1.3 | 607 |
| 2 | 400-nm InGaN-GaN and InGaN-AlGaN multiquantum well light-emitting diodes. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 744-748. | 1.9 | 213 |
| 3 | Effects of thermal annealing on the indium tin oxide Schottky contacts of n-GaN. Applied Physics Letters, 1998, 72, 3317-3319. | 1.5 | 150 |
| 4 | Influence of Si-doping on the characteristics of InGaN-GaN multiple quantum-well blue light emitting diodes. IEEE Journal of Quantum Electronics, 2002, 38, 446-450. | 1.0 | 147 |
| 5 | GaN metal-semiconductor-metal ultraviolet photodetectors with transparent indium-tin-oxide Schottky contacts. IEEE Photonics Technology Letters, 2001, 13, 848-850. | 1.3 | 144 |
| 6 | Low-operation voltage of InGaN-GaN light-emitting diodes with Si-doped In/sub 0.3/Ga/sub 0.7/N/GaN short-period superlattice tunneling contact layer. IEEE Electron Device Letters, 2001, 22, 460-462. | 2.2 | 125 |
| 7 | InGaN-AlInGaN multiquantum-well LEDs. IEEE Photonics Technology Letters, 2001, 13, 559-561. | 1.3 | 100 |
| 8 | GaN metal-semiconductor-metal ultraviolet sensors with various contact electrodes. IEEE Sensors Journal, 2002, 2, 366-371. | 2.4 | 99 |
| 9 | Nitride-Based LEDs With 800<tex>$^circboxC$</tex>Grown p-AlInGaNâ€“GaN Double-Cap Layers. IEEE Photonics Technology Letters, 2004, 16, 1447-1449. | 1.3 | 95 |
| 10 | The doping process and dopant characteristics of GaN. Journal of Physics Condensed Matter, 2002, 14, R657-R702. | 0.7 | 93 |
| 11 | GaN metal-semiconductor-metal photodetectors with low-temperature-GaN cap layers and ITO metal contacts. IEEE Electron Device Letters, 2003, 24, 212-214. | 2.2 | 93 |
| 12 | n-UV+Blue/Green/Red White Light Emitting Diode Lamps. Japanese Journal of Applied Physics, 2003, 42, 2284-2287. | 0.8 | 90 |
| 13 | White-light emission from InGaN-GaN multiquantum-well light-emitting diodes with Si and Zn codoped active well layer. IEEE Photonics Technology Letters, 2002, 14, 450-452. | 1.3 | 86 |
| 14 | Enhanced efficiency of GaN-based light-emitting diodes with periodic textured Ga-doped ZnO transparent contact layer. Applied Physics Letters, 2007, 90, 263511. | 1.5 | 83 |
| 15 | Nitride-based cascade near white light-emitting diodes. IEEE Photonics Technology Letters, 2002, 14, 908-910. | 1.3 | 77 |
| 16 | Nonalloyed Crâˆ•Au-based Ohmic contacts to n-GaN. Applied Physics Letters, 2007, 91, . | 1.5 | 74 |
| 17 | Enhanced light output of GaN-based power LEDs with transparent Al-doped ZnO current spreading layer. IEEE Photonics Technology Letters, 2006, 18, 274-276. | 1.3 | 72 |
| 18 | Nitride-Based LEDs With an SPS Tunneling Contact Layer and an ITO Transparent Contact. IEEE Photonics Technology Letters, 2004, 16, 1002-1004. | 1.3 | 70 |

| # | Article | IF | Citations |
|---|---|---|---|
| 19 | Lateral epitaxial patterned sapphire InGaN/GaN MQW LEDs. Journal of Crystal Growth, 2004, 261, 466-470. | 0.7 | 67 |
| 20 | Nitride-based light emitting diodes with indium tin oxide electrode patterned by imprint lithography. Applied Physics Letters, 2007, 91, 013504. | 1.5 | 67 |
| 21 | High efficiency and improved ESD characteristics of GaN-based LEDs with naturally textured surface grown by MOCVD. IEEE Photonics Technology Letters, 2006, 18, 1213-1215. | 1.3 | 66 |
| 22 | Ohmic contacts to p-type GaN mediated by polarization fields in thin InxGa1â^'xN capping layers. Applied Physics Letters, 2002, 80, 986-988. | 1.5 | 65 |
| 23 | Demonstration of GaN-Based Solar Cells With GaN/InGaN Superlattice Absorption Layers. IEEE Electron Device Letters, 2009, 30, 225-227. | 2.2 | 65 |
| 24 | Improved ESD protection by combining InGaN-GaN MQW LEDs with GaN Schottky diodes. IEEE Electron Device Letters, 2003, 24, 129-131. | 2.2 | 63 |
| 25 | Enhanced AlGaN/GaN MOS-HEMT Performance by Using Hydrogen Peroxide Oxidation Technique. IEEE Transactions on Electron Devices, 2013, 60, 213-220. | 1.6 | 62 |
| 26 | Effect of Thermal Annealing on Ga-Doped ZnO Films Prepared by Magnetron Sputtering. Journal of the Electrochemical Society, 2007, 154, H521. | 1.3 | 61 |
| 27 | InGaN/GaN light emitting diodes activated in O/sub 2/ ambient. IEEE Electron Device Letters, 2002, 23, 240-242. | 2.2 | 60 |
| 28 | High-Speed GaN-Based Green Light-Emitting Diodes With Partially n-Doped Active Layers and Current-Confined Apertures. IEEE Electron Device Letters, 2008, 29, 158-160. | 2.2 | 60 |
| 29 | High-efficiency InGaN-GaN MQW green light-emitting diodes with CART and DBR structures. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 284-288. | 1.9 | 59 |
| 30 | In0.23Ga0.77N/GaN MQW LEDs with a low temperature GaN cap layer. Solid-State Electronics, 2003, 47, 2027-2030. | 0.8 | 58 |
| 31 | ICP etching of sapphire substrates. Optical Materials, 2005, 27, 1171-1174. | 1.7 | 58 |
| 32 | Carrier dynamics in nitride-based light-emitting p-n junction diodes with two active regions emitting at different wavelengths. Journal of Applied Physics, 2003, 94, 2167-2172. | 1.1 | 57 |
| 33 | Effect of low-temperature-grown GaN cap layer on reduced leakage current of GaN Schottky diodes. Applied Physics Letters, 2005, 86, 052103. | 1.5 | 53 |
| 34 | Enhanced output power in GaN-based LEDs with naturally textured surface grown by MOCVD. IEEE Electron Device Letters, 2005, 26, 464-466. | 2.2 | 53 |
| 35 | High brightness green light emitting diodes with charge asymmetric resonance tunneling structure. IEEE Electron Device Letters, 2002, 23, 130-132. | 2.2 | 52 |
| 36 | n+-GaN formed by Si implantation intop-GaN. Journal of Applied Physics, 2002, 91, 1845-1848. | 1.1 | 52 |

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| 37 | InGaN/GaN tunnel-injection blue light-emitting diodes. IEEE Transactions on Electron Devices, 2002, 49, 1093-1095. | 1.6 | 52 |
| 38 | Nitride-based near-ultraviolet LEDs with an ITO transparent contact. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 106, 69-72. | 1.7 | 52 |
| 39 | Enhancement in light output of InGaN-based microhole array light-emitting diodes. IEEE Photonics Technology Letters, 2005, 17, 1163-1165. | 1.3 | 50 |
| 40 | A curvature-tunable random laser. Nanoscale, 2019, 11, 3534-3545. | 2.8 | 50 |
| 41 | GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. Applied Physics Letters, 2003, 82, 2913-2915. | 1.5 | 46 |
| 42 | Schottky barrier heights of metal contacts to n-type gallium nitride with low-temperature-grown cap layer. Applied Physics Letters, 2006, 88, 032103. | 1.5 | 45 |
| 43 | Probing Hydrophilic Interface of Solid/Liquid-Water by Nanoultrasonics. Scientific Reports, 2014, 4, 6249. | 1.6 | 45 |
| 44 | Low-operation voltage of InGaN/GaN light-emitting diodes by using a Mg-doped Al/sub 0.15/Ga/sub 0.85/N/GaN superlattice. IEEE Electron Device Letters, 2001, 22, 160-162. | 2.2 | 44 |
| 45 | Electroluminescence efficiency of blue InGaNâ•GaN quantum-well diodes with and without an n-InGaN electron reservoir layer. Journal of Applied Physics, 2006, 100, 113105. | 1.1 | 44 |
| 46 | THz acoustic phonon spectroscopy and nanoscopy by using piezoelectric semiconductor heterostructures. Ultrasonics, 2015, 56, 52-65. | 2.1 | 44 |
| 47 | InGaN light-emitting diodes with naturally formed truncated micropyramids on top surface. Applied Physics Letters, 2006, 88, 113505. | 1.5 | 43 |
| 48 | Enhancement in output power of blue gallium nitride-based light-emitting diodes with omnidirectional metal reflector under electrode pads. Applied Physics Letters, 2008, 93, 103507. | 1.5 | 43 |
| 49 | Planar GaN n+â€“p photodetectors formed by Si implantation into p-GaN. Applied Physics Letters, 2002, 81, 4263-4265. | 1.5 | 42 |
| 50 | GaN-Based Miniaturized Cyan Light-Emitting Diodes on a Patterned Sapphire Substrate With Improved Fiber Coupling for Very High-Speed Plastic Optical Fiber Communication. IEEE Photonics Journal, 2012, 4, 1520-1529. | 1.0 | 42 |
| 51 | Investigation of the mechanism for Ti/Al ohmic contact on etched n-GaN surfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 729. | 1.6 | 39 |
| 52 | Enhanced output power in an InGaN-GaN multiquantum-well light-emitting diode with an InGaN current-spreading layer. IEEE Photonics Technology Letters, 2001, 13, 1164-1166. | 1.3 | 39 |
| 53 | High-performance GaN metalâ€“insulatorâ€“semiconductor ultraviolet photodetectors using gallium oxide as gate layer. Optics Express, 2011, 19, 12658. | 1.7 | 39 |
| 54 | Nitride-Based LEDs With Modulation-Doped Al<tex>$_0.12hbox Ga_0.88 hbox N$</tex>â€“GaN Superlattice Structures. IEEE Transactions on Electron Devices, 2004, 51, 1743-1746. | 1.6 | 38 |

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| 55 | Effect of Thickness of the p-AlGaN Electron Blocking Layer on the Improvement of ESD Characteristics in GaN-Based LEDs. IEEE Photonics Technology Letters, 2008, 20, 1142-1144. | 1.3 | 38 |
| 56 | Improvement of near-ultraviolet InGaN-GaN light-emitting diodes with an AlGaN electron-blocking layer grown at low temperature. IEEE Photonics Technology Letters, 2003, 15, 1342-1344. | 1.3 | 37 |
| 57 | Characterization of GaN Schottky barrier photodetectors with a low-temperature GaN cap layer. Journal of Applied Physics, 2003, 94, 1753-1757. | 1.1 | 37 |
| 58 | Reduction of Dark Current in AlGaNâ€“GaN Schottky-Barrier Photodetectors With a Low-Temperature-Grown GaN Cap Layer. IEEE Electron Device Letters, 2004, 25, 593-595. | 2.2 | 37 |
| 59 | Improved Reliability and ESD Characteristics of Flip-Chip GaN-Based LEDs With Internal Inverse-Parallel Protection Diodes. IEEE Electron Device Letters, 2007, 28, 346-349. | 2.2 | 37 |
| 60 | Laser-induced periodic structures for light extraction efficiency enhancement of GaN-based light emitting diodes. Optics Express, 2012, 20, 5689. | 1.7 | 36 |
| 61 | Indium tin oxide ohmic contact to highly doped n-GaN. Solid-State Electronics, 1999, 43, 2081-2084. | 0.8 | 35 |
| 62 | Emission Mechanism of Mixed-Color InGaN/GaN Multi-Quantum-Well Light-Emitting Diodes. Japanese Journal of Applied Physics, 2006, 45, 2463-2466. | 0.8 | 35 |
| 63 | Characterization of Si implants in p-type GaN. IEEE Journal of Selected Topics in Quantum Electronics, 2002, 8, 767-772. | 1.9 | 34 |
| 64 | Improved Performance of GaN-Based Blue LEDs With the InGaN Insertion Layer Between the MQW Active Layer and the n-GaN Cladding Layer. IEEE Journal of Quantum Electronics, 2010, 46, 513-517. | 1.0 | 34 |
| 65 | Luminescence of an InGaN/GaN multiple quantum well light-emitting diode. Solid-State Electronics, 2000, 44, 1055-1058. | 0.8 | 32 |
| 66 | The improvement in modulation speed of GaN-based Green light-emitting diode (LED) by use of n-type barrier doping for plastic optical fiber (POF) communication. IEEE Photonics Technology Letters, 2006, 18, 1636-1638. | 1.3 | 32 |
| 67 | Ga-Doped ZnO Transparent Conductive Oxide Films Applied to GaN-Based Light-Emitting Diodes for Improving Light Extraction Efficiency. IEEE Journal of Quantum Electronics, 2008, 44, 1211-1218. | 1.0 | 32 |
| 68 | Design of Hole-Blocking and Electron-Blocking Layers in Al<sub>x</sub>Ga<sub>1-x</sub>N-Based UV Light-Emitting Diodes. IEEE Transactions on Electron Devices, 2016, 63, 1141-1147. | 1.6 | 32 |
| 69 | InGaN-based epitaxial films as photoelectrodes for hydrogen generation through water photoelectrolysis and CO2 reduction to formic acid. Solar Energy Materials and Solar Cells, 2017, 166, 86-90. | 3.0 | 32 |
| 70 | Si and Zn co-doped InGaN-GaN white light-emitting diodes. IEEE Transactions on Electron Devices, 2003, 50, 519-521. | 1.6 | 31 |
| 71 | Improving efficiency of InGaN/GaN multiple quantum well solar cells using CdS quantum dots and distributed Bragg reflectors. Solar Energy Materials and Solar Cells, 2013, 117, 531-536. | 3.0 | 31 |
| 72 | Sea-Urchin-Like Bi<sub>2</sub>S<sub>3</sub> Microstructures Decorated with Graphitic Carbon Nitride Nanosheets for Use in Food Preservation. ACS Applied Nano Materials, 2022, 5, 2375-2384. | 2.4 | 31 |

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| 73 | Ultraviolet band-pass Schottky barrier photodetectors formed by Al-doped ZnO contacts to n-GaN. Applied Physics Letters, 2006, 88, 043506. | 1.5 | 30 |
| 74 | Effect of the Electrode Pattern on Current Spreading and Driving Voltage in a GaNâˆ•Sapphire LED Chip. Journal of the Electrochemical Society, 2008, 155, H836. | 1.3 | 30 |
| 75 | III-Nitride Based Cyan Light-Emitting Diodes with GHz Bandwidth for High-Speed Visible Light Communication. IEEE Electron Device Letters, 2016, , 1-1. | 2.2 | 30 |
| 76 | GaN-based p-i-n sensors with ITO contacts. IEEE Sensors Journal, 2006, 6, 406-411. | 2.4 | 29 |
| 77 | High brightness ingan green leds with an ito on n/sup ++/ -sps upper contact. IEEE Transactions on Electron Devices, 2003, 50, 2208-2212. | 1.6 | 28 |
| 78 | Inverted Al0.25Ga0.75N/GaN ultraviolet p-i-n photodiodes formed on p-GaN template layer grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2010, 97, 013502. | 1.5 | 27 |
| 79 | GaN-based light emitting diodes with embedded SiO2 pillars and air gap array structures. Applied Physics Letters, 2010, 97, . | 1.5 | 27 |
| 80 | Enhancement of the conversion efficiency of GaN-based photovoltaic devices with AlGaN/InGaN absorption layers. Applied Physics Letters, 2010, 97, 021113. | 1.5 | 27 |
| 81 | Slanted n-ZnO/p-GaN nanorod arrays light-emitting diodes grown by oblique-angle deposition. APL Materials, 2014, 2, 056101. | 2.2 | 27 |
| 82 | Enhancing UV-emissions through optical and electronic dual-function tuning of Ag nanoparticles hybridized with n-ZnO nanorods/p-GaN heterojunction light-emitting diodes. Nanoscale, 2016, 8, 4463-4474. | 2.8 | 27 |
| 83 | Ultraviolet bandpass Al0.17Ga0.83Nâˆ•GaN heterojunction phototransitors with high optical gain and high rejection ratio. Applied Physics Letters, 2008, 92, . | 1.5 | 26 |
| 84 | Effects of Thermal Annealing on Al-Doped ZnO Films Deposited on p-Type Gallium Nitride. Journal of the Electrochemical Society, 2006, 153, G296. | 1.3 | 25 |
| 85 | Photodetectors formed by an indium tin oxide/zinc oxide/p-type gallium nitride heterojunction with high ultraviolet-to-visible rejection ratio. Applied Physics Letters, 2009, 94, 013512. | 1.5 | 25 |
| 86 | Low Operation Voltage of Nitride-Based LEDs with Al-Doped ZnO Transparent Contact Layer. Electrochemical and Solid-State Letters, 2008, 11, H269. | 2.2 | 24 |
| 87 | A Numerical Study of Thermal and Electrical Effects in a Vertical LED Chip. Journal of the Electrochemical Society, 2010, 157, H31. | 1.3 | 24 |
| 88 | Rationally designed RGO@CuO@Mn<sub>2</sub>O<sub>3</sub>as an excellent electrocatalyst for the rapid and real-time detection of 2-nitrophenol. New Journal of Chemistry, 2020, 44, 12465-12472. | 1.4 | 24 |
| 89 | Nitride-based green light-emitting diodes with high temperature GaN barrier layers. IEEE Transactions on Electron Devices, 2003, 50, 1766-1770. | 1.6 | 23 |
| 90 | Ga<sub>2</sub>O<sub>3</sub>Films for Photoelectrochemical Hydrogen Generation. Journal of the Electrochemical Society, 2014, 161, H508-H511. | 1.3 | 23 |

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| 91 | White emission from non-planar InGaN/GaN MQW LEDs grown on GaN template with truncated hexagonal pyramids. Optics Express, 2015, 23, A401. | 1.7 | 23 |
| 92 | Observation of dislocation etch pits in epitaxial lateral overgrowth GaN by wet etching. Solid-State Electronics, 2002, 46, 555-558. | 0.8 | 22 |
| 93 | Femtosecond ultrasonic spectroscopy using a piezoelectric nanolayer: Hypersound attenuation in vitreous silica films. Applied Physics Letters, 2011, 99, 051913. | 1.5 | 22 |
| 94 | Nitride-based blue LEDs with GaN/SiN double buffer layers. Solid-State Electronics, 2003, 47, 2019-2022. | 0.8 | 21 |
| 95 | InGaN gallium nitride light-emitting diodes with reflective electrode pads and textured gallium-doped ZnO contact layer. Applied Physics Letters, 2010, 96, 133504. | 1.5 | 21 |
| 96 | Light-emitting diodes with surface gallium nitride pâ€“n homojunction structure formed by selective area regrowth. Scientific Reports, 2019, 9, 3243. | 1.6 | 21 |
| 97 | GaN pâ€“n junction diode formed by Si ion implantation into p-GaN. Solid-State Electronics, 2002, 46, 2179-2183. | 0.8 | 20 |
| 98 | Deep level defect in Si-implanted GaNâ€Šn+-p junction. Applied Physics Letters, 2003, 82, 3671-3673. | 1.5 | 20 |
| 99 | Experimental study of perpendicular transport in weakly coupled AlxGa1â^'xN/GaN superlattices. Applied Physics Letters, 2003, 83, 4975-4977. | 1.5 | 20 |
| 100 | Comparison of low-temperature GaN, SiO2, and SiNx as gate insulators on AlGaNâ•GaN heterostructure field-effect transistors. Journal of Applied Physics, 2005, 98, 064506. | 1.1 | 20 |
| 101 | Electrical-optical analysis of a GaN/sapphire LED chip by considering the resistivity of the current-spreading layer. Optical Review, 2009, 16, 213-215. | 1.2 | 20 |
| 102 | Vertical InGaN-based green-band solar cells operating under high solar concentration up to 300 suns. Optics Express, 2014, 22, A1222. | 1.7 | 20 |
| 103 | Ultraviolet/blue light-emitting diodes based on single horizontal ZnO microrod/GaN heterojunction. Nanoscale Research Letters, 2014, 9, 446. | 3.1 | 20 |
| 104 | Mn valence state mediated room temperature ferromagnetism in nonpolar Mn doped GaN. Applied Surface Science, 2019, 473, 693-698. | 3.1 | 20 |
| 105 | Visibleâ€“blind GaN pâ€“iâ€“n photodiodes with an Al0.12Ga0.88N/GaN superlattice structure. Solid-State Electronics, 2003, 47, 873-878. | 0.8 | 19 |
| 106 | Phosphor-Free GaN-Based Transverse Junction Light Emitting Diodes for the Generation of White Light. IEEE Photonics Technology Letters, 2006, 18, 2593-2595. | 1.3 | 19 |
| 107 | AlGaN ultraviolet metal-semiconductor-metal photodetectors grown on Si substrates. Sensors and Actuators A: Physical, 2007, 135, 502-506. | 2.0 | 19 |
| 108 | GaN-Based LEDs With AZO:Y Upper Contact. IEEE Transactions on Electron Devices, 2010, 57, 134-139. | 1.6 | 19 |

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| 109 | Improved conversion efficiency of GaN-based solar cells with Mn-doped absorption layer. Applied Physics Letters, 2013, 103, 063906. | 1.5 | 19 |
| 110 | Passively gain-switched and self mode-locked thulium fiber laser at 1950nm. Optics and Laser Technology, 2014, 56, 354-357. | 2.2 | 19 |
| 111 | Polymer PBT/n-GaN metalâ€“insulatorâ€“semiconductor structure. Applied Physics Letters, 2001, 79, 4589-4591. | 1.5 | 18 |
| 112 | High-Responsivity Solar-Blind Photodetectors Formed by Ga<sub>2</sub>O<sub>3</sub>/p-GaN Bipolar Heterojunctions. ACS Photonics, 2022, 9, 1002-1007. | 3.2 | 18 |
| 113 | Temperature-dependent study of n-ZnOâˆ•p-GaN diodes. Applied Physics Letters, 2007, 90, 132111. | 1.5 | 17 |
| 114 | Ultraviolet band-pass photodetectors formed by Ga-doped ZnO contacts to n-GaN. Applied Physics Letters, 2008, 92, 113512. | 1.5 | 17 |
| 115 | Characteristics of InGaN-based concentrator solar cells operating under 150X solar concentration. Optics Express, 2011, 19, A695. | 1.7 | 17 |
| 116 | Thermal Boundary Resistance between GaN and Cubic Ice and THz Acoustic Attenuation Spectrum of Cubic Ice from Complex Acoustic Impedance Measurements. Physical Review Letters, 2013, 111, 225901. | 2.9 | 17 |
| 117 | AlGaN-based deep ultraviolet light emitting diodes with magnesium delta-doped AlGaN last barrier. Applied Physics Letters, 2020, 117, . | 1.5 | 17 |
| 118 | Low-resistance Ni/Au ohmic contact to Mg-doped of Al0.15Ga0.85N/GaN superlattices. Solid-State Electronics, 2001, 45, 717-720. | 0.8 | 16 |
| 119 | Effect of Cl2âˆ•Ar dry etching on p-GaN with Niâˆ•Au metallization characterization. Applied Physics Letters, 2005, 87, 252107. | 1.5 | 16 |
| 120 | Improved Output Power of GaN-based Blue LEDs by Forming Air Voids on Ar-Implanted Sapphire Substrate. Journal of Lightwave Technology, 2013, 31, 1318-1322. | 2.7 | 16 |
| 121 | Warm-white light-emitting diode with high color rendering index fabricated by combining trichromatic InGaN emitter with single red phosphor. Optics Express, 2015, 23, A232. | 1.7 | 16 |
| 122 | Manganese-doped AlGaN/GaN heterojunction solar cells with intermediate band absorption. Solar Energy Materials and Solar Cells, 2016, 157, 727-732. | 3.0 | 16 |
| 123 | Linear Cascade Arrays of GaN-Based Green Light-Emitting Diodes for High-Speed and High-Power Performance. IEEE Photonics Technology Letters, 2007, 19, 1368-1370. | 1.3 | 15 |
| 124 | Improvement of InGaN/GaN laser diodes by using a Si-doped In/sub 0.23/Ga/sub 0.77/N/GaN short-period superlattice tunneling contact layer. IEEE Electron Device Letters, 2003, 24, 206-208. | 2.2 | 14 |
| 125 | Si diffusion in p-GaN. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1727. | 1.6 | 14 |
| 126 | Investigation of the Carrier Dynamic in GaN-Based Cascade Green Light-Emitting Diodes Using the Very Fast Electricalâ€“Optical Pumpâ€“Probe Technique. IEEE Transactions on Electron Devices, 2011, 58, 495-500. | 1.6 | 14 |

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| 127 | Mn-doped GaN as photoelectrodes for the photoelectrolysis of water under visible light. Optics Express, 2012, 20, A678. | 1.7 | 14 |
| 128 | GaN-Based Planar p-i-n Photodetectors With the Be-Implanted Isolation Ring. IEEE Transactions on Electron Devices, 2013, 60, 1178-1182. | 1.6 | 14 |
| 129 | High-power and single-mode VCSEL arrays with single-polarized outputs by using package-induced tensile strain. Optics Letters, 2020, 45, 4839. | 1.7 | 14 |
| 130 | Highly Reliable Nitride-Based LEDs With Internal ESD Protection Diodes. IEEE Transactions on Device and Materials Reliability, 2006, 6, 442-447. | 1.5 | 13 |
| 131 | Improved performance of planar GaN-based p-i-n photodetectors with Mg-implanted isolation ring. Applied Physics Letters, 2006, 89, 183509. | 1.5 | 13 |
| 132 | AlGaN/GaN Schottky-barrier UV-B bandpass photodetectors with ITO contacts and LT-GaN cap layers. Semiconductor Science and Technology, 2006, 21, 1064-1068. | 1.0 | 13 |
| 133 | Phosphor-Free GaN-Based Transverse Junction White-Light Light-Emitting Diodes With Regrown n-Type Regions. IEEE Photonics Technology Letters, 2008, 20, 449-451. | 1.3 | 13 |
| 134 | GaN-Based LEDs Output Power Improved by Textured GaN/Sapphire Interface Using <emphasis emphasistype="italic">In Situ</emphasis> <formula formulatype="inline"><tex Notation="TeX">$hbox{SiH}_{f 4}$</tex> </formula> Treatment Process During Epitaxial Growth. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1275-1280. | 1.9 | 13 |
| 135 | Hydrogen gas generation using n-GaN photoelectrodes with immersed Indium Tin Oxide ohmic contacts. Optics Express, 2011, 19, A1196. | 1.7 | 13 |
| 136 | Femtosecond excitation of radial breathing mode in 2-D arrayed GaN nanorods. Optics Express, 2012, 20, 16611. | 1.7 | 13 |
| 137 | GaN-based light emitting diodes with micro- and nano-patterned structures by femtosecond laser nonlinear decomposition. Applied Physics Letters, 2012, 101, 131103. | 1.5 | 13 |
| 138 | Characterization of p-type InxGa1âˆ’xN grown by metalorganic chemical vapor deposition. Solid-State Electronics, 2001, 45, 427-430. | 0.8 | 12 |
| 139 | Linear Cascade GaN-Based Green Light-Emitting Diodes With Invariant High-Speed/Power Performance Under High-Temperature Operation. IEEE Photonics Technology Letters, 2008, 20, 1896-1898. | 1.3 | 12 |
| 140 | High-Brightness InGaNâ€“GaN Power Flip-Chip LEDs. Journal of Lightwave Technology, 2009, 27, 1985-1989. | 2.7 | 12 |
| 141 | Femtosecond laser-ultrasonic investigation of plasmonic fields on the metal/gallium nitride interface. Applied Physics Letters, 2010, 97, . | 1.5 | 12 |
| 142 | Effect of Growth Pressure of Undoped GaN Layer on the ESD Characteristics of GaN-Based LEDs Grown on Patterned Sapphire. IEEE Photonics Technology Letters, 2011, 23, 968-970. | 1.3 | 12 |
| 143 | Influence of modulated fields on the Landau level properties of graphene. Physical Review B, 2011, 83, . | 1.1 | 12 |
| 144 | Gallium nitride-based light-emitting diodes with embedded air voids grown on Ar-implanted AlN/sapphire substrate. Applied Physics Letters, 2012, 101, . | 1.5 | 12 |

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| 145 | InGaN working electrodes with assisted bias generated from GaAs solar cells for efficient water splitting. Optics Express, 2013, 21, A991. | 1.7 | 12 |
| 146 | In Situ Monitoring of Chemical Reactions at a Solidâ€“Water Interface by Femtosecond Acoustics. Journal of Physical Chemistry Letters, 2017, 8, 5430-5437. | 2.1 | 12 |
| 147 | AlGaInP/GaP Light-Emitting Diodes Fabricated by Wafer Direct Bonding Technology. Japanese Journal of Applied Physics, 1996, 35, 4199-4202. | 0.8 | 11 |
| 148 | GaN diffractive microlenses fabricated with gray-level mask. Optics Communications, 2003, 215, 75-78. | 1.0 | 11 |
| 149 | GaInN light-emitting diodes with omnidirectional reflectors. , 2003, 4996, 139. | | 11 |
| 150 | Improved Light Extraction Efficiency in AlGaInP Light-Emitting Diodes by Applying a Periodic Texture on the Surface. IEEE Photonics Technology Letters, 2008, 20, 1724-1726. | 1.3 | 11 |
| 151 | The Structure of GaN-Based Transverse Junction Blue LED Array for Uniform Distribution of Injected Current/Carriers. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1292-1297. | 1.9 | 11 |
| 152 | Improved Hydrogen Gas Generation Rate of n-GaN Photoelectrode with SiO[sub 2] Protection Layer on the Ohmic Contacts from the Electrolyte. Journal of the Electrochemical Society, 2010, 157, B266. | 1.3 | 11 |
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